

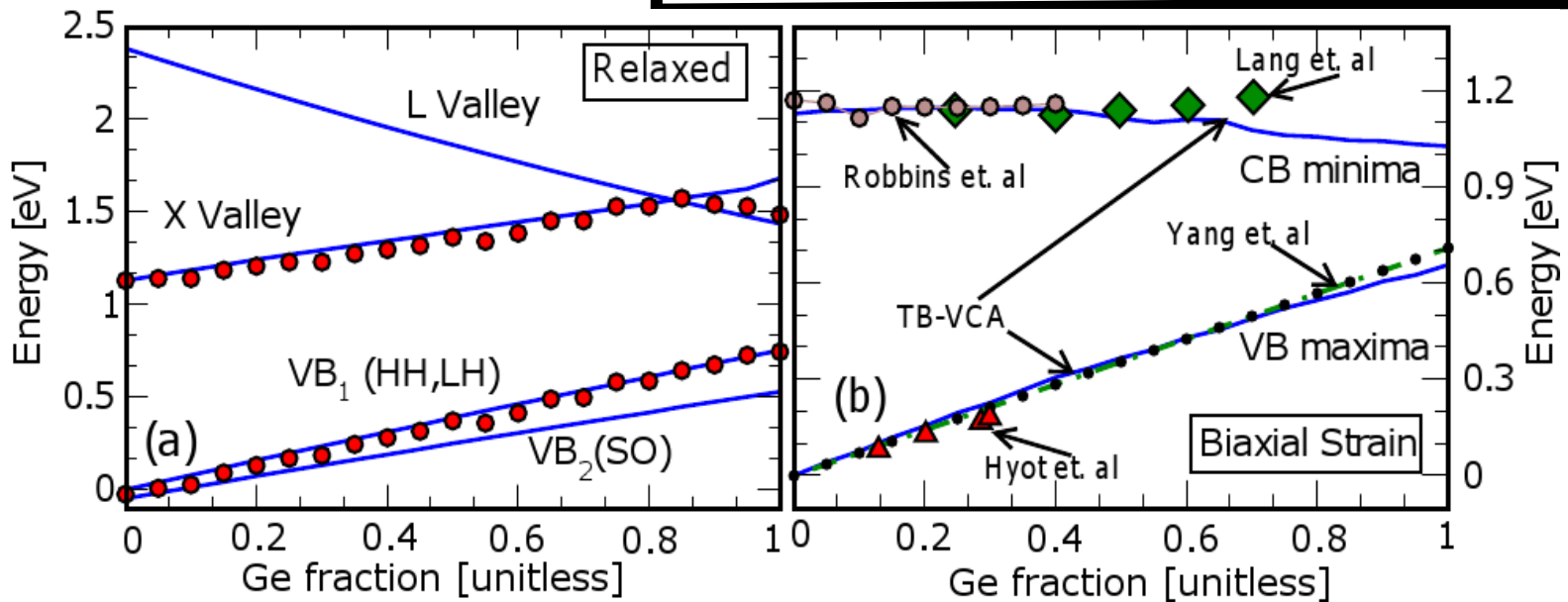
Objective: Bandstructure model for SiGe mosFETS. (higher hole and electron mobility compared to Si).

Results:

Matched experimental data for relaxed and strained band-edges in SiGe bulk.

Approach:

- Virtual Crystal Approximation in TB (TB-VCA):
 - ✓ Adjust bond-length for internal strain.
 - ✓ TB Hamiltonian accounting for internal and external strain.



Impact: Published in IEEE, EDL, 31, 2010. doi: 10.1109/LED.2010.2040577